

# 2STD1665

## Low voltage fast-switching NPN power transistor

### Features

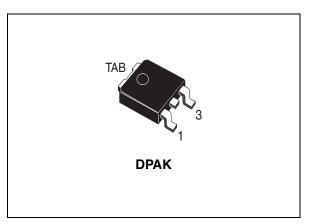
- Very low collector to emitter saturation voltage
- High current gain characteristic
- Fast-switching speed

### Applications

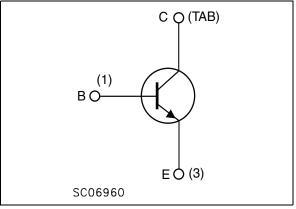
- Voltage regulators
- High efficiency low voltage switching applications

### Description

The device is a low voltage NPN transistor with exceptional high gain performance coupled with very low saturation voltage. It is designed in planar technology with "base island" layout.



#### Figure 1. Internal schematic diagram



#### Table 1. Device summary

Order code	Marking	Packages	Packaging
2STD1665T4	D1665	DPAK	Tape and reel

# 1 Electrical ratings

Table 2.	Absolute maximum ratings	
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Symbol	Parameter	Value	Unit
V <sub>CBO</sub>	Collector-base voltage (I <sub>E</sub> = 0)	150	V
$V_{CEO}$	Collector-emitter voltage ( $I_B = 0$ )	65	V
$V_{\text{EBO}}$	Emitter-base voltage (I <sub>C</sub> = 0)	7	V
۱ <sub>C</sub>	Collector current	6	А
I <sub>CM</sub>	Collector peak current (t <sub>P</sub> < 5ms)	20	А
Ι <sub>Β</sub>	Base current	1	А
P <sub>tot</sub>	Total dissipation at $T_a = 25 \ ^{\circ}C$	15	W
T <sub>stg</sub>	Storage temperature	-65 to 150	°C
Τ <sub>J</sub>	Max. operating junction temperature	150	°C

#### Table 3. Thermal data

Rthermal resistance junction-ambientmax8.33°C/W	Symbol	Parameter	Value	Unit
	R <sub>thj-a</sub> <sup>(1)</sup>	Thermal resistance junction-ambient max	8.33	°C/W

1. Device mounted on a PCB area of 1  $\text{cm}^2$ 



## 2 Electrical characteristics

 $(T_{case} = 25^{\circ}C \text{ unless otherwise specified}).$ 

Symbol	Parameter	Test conditions		Min.	Тур.	vp. Max.	Unit
Symbol			onations		Typ.	-	
I <sub>CBO</sub>	Collector cut-off current $(I_F = 0)$	V <sub>CB</sub> = 120 V V <sub>CB</sub> = 120 V	T <sub>o</sub> = 100 °C			50 1	nΑ μΑ
I <sub>EBO</sub>	Emitter cut-off current $(I_{C} = 0)$	V <sub>EB</sub> = 7 V				10	nA
V <sub>(BR)CBO</sub> <sup>(1)</sup>	Collector-base breakdown voltage (I <sub>E</sub> = 0)	l <sub>C</sub> = 100 μA		150			v
V <sub>(BR)CEO</sub> <sup>(1)</sup>	Collector-emitter breakdown voltage (I <sub>B</sub> = 0)	I <sub>C</sub> = 10 mA		65			v
V <sub>(BR)EBO</sub> <sup>(1)</sup>	Emitter-base breakdown voltage (I <sub>C</sub> = 0)	l <sub>E</sub> = 100 μA		7			v
V <sub>CE(sat)</sub> <sup>(1)</sup>	Collector-emitter saturation voltage	$I_{C} = 100 \text{ mA}$ $I_{C} = 1 \text{ A}$ $I_{C} = 2 \text{ A}$ $I_{C} = 6 \text{ A}$ $I_{C} = 6 \text{ A}$	I <sub>B</sub> = 5 mA I <sub>B</sub> = 50 mA I <sub>B</sub> = 50 mA I <sub>B</sub> = 150 mA I <sub>B</sub> = 300 mA		50 100 260 230	50 120 200 600 380	mV mV mV mV mV
V <sub>BE(sat)</sub> <sup>(1)</sup>	Base-emitter saturation voltage	I <sub>C</sub> = 4 A	I <sub>B</sub> = 200 mA		1	1.15	V
V <sub>BE(on)</sub> <sup>(1)</sup>	Base-emitter on voltage	I <sub>C</sub> = 4 A	V <sub>CE</sub> = 1 V		0.85	1	V
h <sub>FE</sub>	DC current gain	$I_{C} = 10 \text{ mA}$ $I_{C} = 2 \text{ A}$ $I_{C} = 5 \text{ A}$ $I_{C} = 10 \text{ A}$	$V_{CE} = 1 V$	150 150 90 30	320 310 175 65	350	
C <sub>CBO</sub>	Collector-base capacitance (I <sub>E</sub> =0)	V <sub>CB</sub> = 10 V	f = 1 MHz		45		pF
t <sub>on</sub> t <sub>s</sub> t <sub>f</sub>	Resistive load Turn-on time Storage time Fall time	$I_{C} = 3 \text{ A}$ $I_{B(on)} = -I_{B(off)} =$ $V_{BB(off)} = -5 \text{ V}$	V <sub>CC</sub> = 10 V = 300 mA		90 800 90		ns ns ns

#### Table 4. Electrical characteristics

1. Pulse test: pulse duration  $\leq$  300  $\mu s,$  duty cycle  $\leq$  2 %



V<sub>CE (sat)</sub> (V)

0.1

0.01

0.001

h <sub>FE</sub> =20

### 2.1 Electrical characteristics (curves)

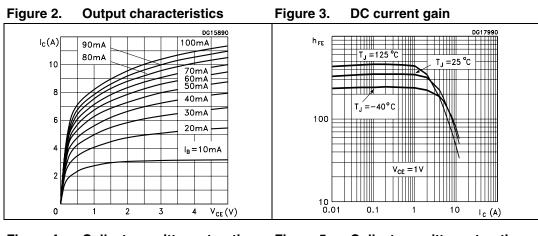


Figure 4. Collector-emitter saturation voltage - (h<sub>FE</sub> = 20)

T<sub>J</sub> =125 °C

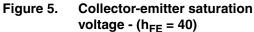
 $T_J = -40^{\circ}C$ 

1

10

I<sub>c</sub> (A)

T<sub>J</sub> = 25



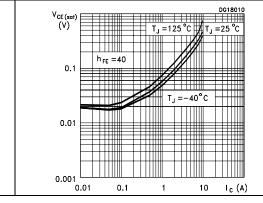
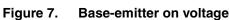
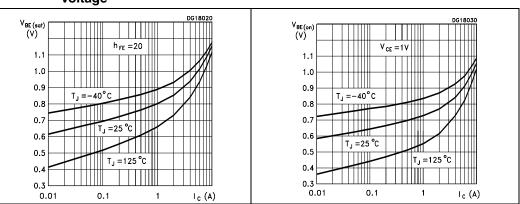


Figure 6. Base-emitter saturation voltage

0.1



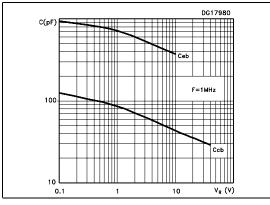




DG17960 DG17970 t(ns) † (n s)  $I_{B(on)} = -I_{B(off)}$ h<sub>FE</sub> = 10  $V_{cc} = 10V$  $V_{cc} = 10V$ 80 V<sub>BB(off)</sub>=-5V  $V_{BB(off)} = -5V$ t,  $I_{B(on)} = -I_{B(off)}$  $h_{FE} = 10$ 70 t, 1000 60 50 t<sub>f</sub> 40 100 30 t<sub>d</sub> 20 10 L 0 10 L 0 0.5 1.5 I<sub>C</sub> (A) 1 2 2.5 0.5 1 1.5 2 2.5  $I_{C}$  (A)

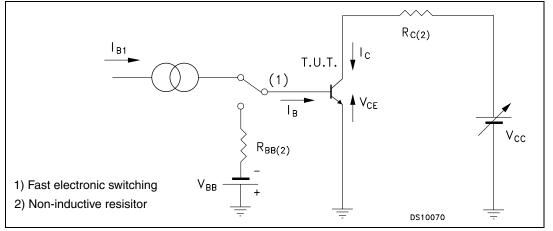
Figure 8. Resistive load switching off Figure 9. Resistive load switching on





### 2.2 Test circuit

#### Figure 11. Resistive load switching time



## 3 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.





Dim. —	mm			
	Min.	Тур.	Max.	
А	2.20		2.40	
A1	0.90		1.10	
A2	0.03		0.23	
b	0.64		0.90	
b4	5.20		5.40	
С	0.45		0.60	
c2	0.48		0.60	
D	6.00		6.20	
D1		5.10		
E	6.40		6.60	
E1		4.70		
е		2.28		
e1	4.40		4.60	
Н	9.35		10.10	
L	1			
L1		2.80		
L2		0.80		
L4	0.60		1	
R		0.20		
V2	<b>0</b> °		8°	

 Table 5.
 DPAK (TO-252) mechanical data



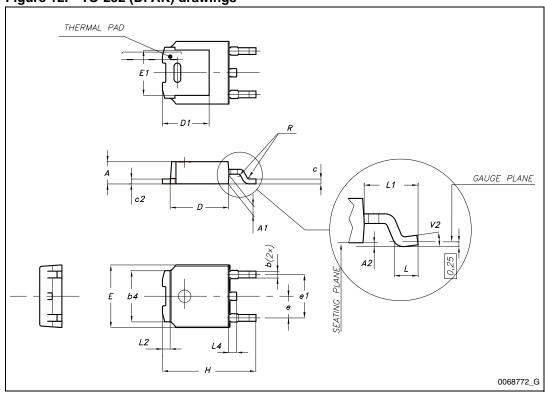


Figure 12. TO-252 (DPAK) drawings



## 4 Revision history

#### Table 6.Document revision history

Date	Revision	Changes
08-May-2006	1	Initial release
27-Mar-2008	2	New graphics
08-Feb-2011	3	Updated Table 2 and 3



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